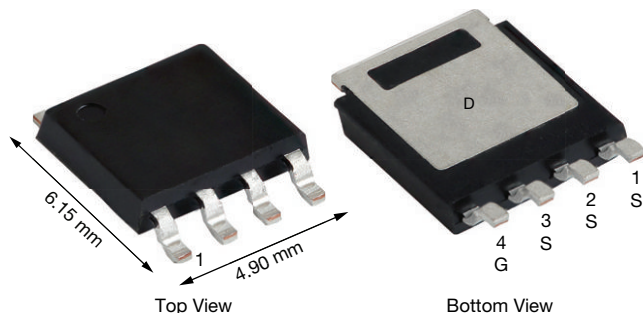


Automotive P-Channel 40 V (D-S) 175 °C MOSFET

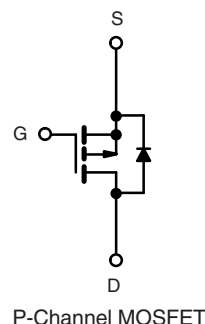
PowerPAK® SO-8L


FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0070
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.0100
I_D (A) ^g	-98
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ149ELP (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-40	V	
Gate-source voltage ^a	V_{GS}	± 20	V	
Continuous drain current ^g	$T_C = 25$ °C ^b $T_C = 125$ °C	-98	A	
		-57		
Continuous source current (diode conduction) ^{b, g}	I_S	-124		
Pulsed drain current ^{c, g}	I_{DM}	-350		
Single pulse avalanche current	I_{AS}	-40		
Single pulse avalanche energy	E_{AS}	80	mJ	
Maximum power dissipation ^{c, g}	$T_C = 25$ °C $T_C = 125$ °C	136	W	
		45		
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R_{thJA}	42	°C/W	
Junction-to-case (drain) ^f	R_{thJC}	1.1		

Notes

- Not intended for continuous use with positive gate voltage > 5.0 V
- Package limited
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- Using thermal characterization methods based on JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system

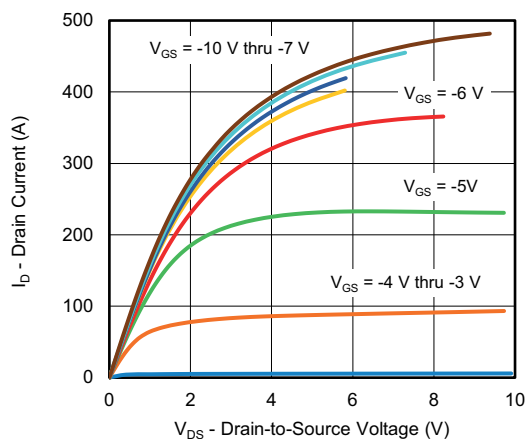
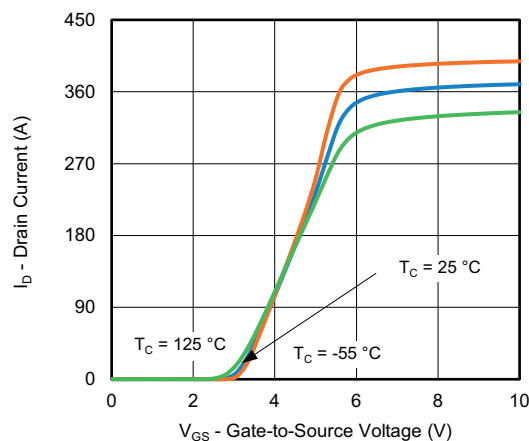
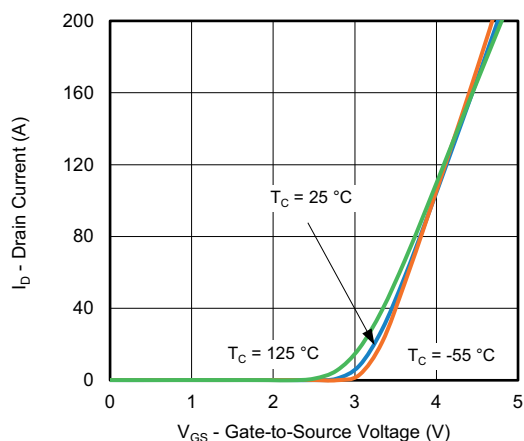
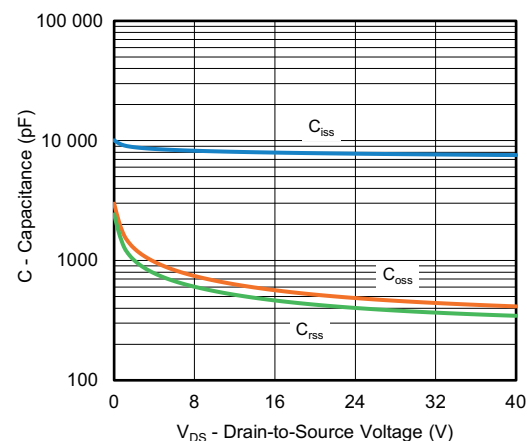
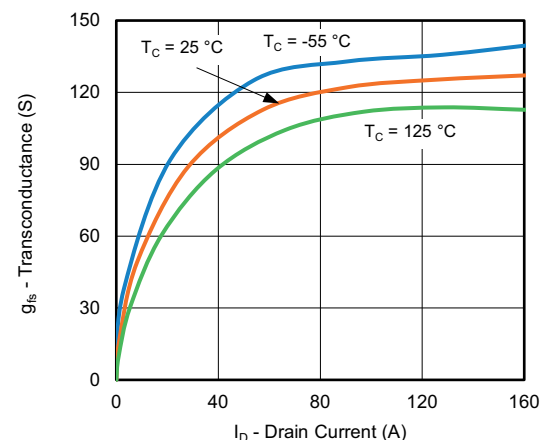
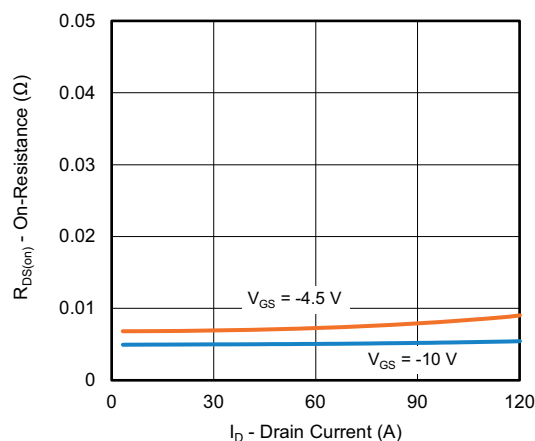


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≥ -5 V	-30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A	-	0.0052	0.0070	Ω
		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0115	
		V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.015	
		V _{GS} = -4.5 V	I _D = -8 A	-	0.0073	0.0100	
Forward transconductance ^b	g _{fs}	V _{DS} = -15 V, I _D = -30 A		-	90	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	7786	10 901	pF
Output capacitance	C _{oss}			-	479	671	
Reverse transfer capacitance	C _{rss}			-	397	556	
Total gate charge ^c	Q _g	V _{GS} = -10 V	V _{DS} = -20 V, I _D = -10 A	-	139	209	nC
Gate-source charge ^c	Q _{gs}			-	26	-	
Gate-drain charge ^c	Q _{gd}			-	24	-	
Gate resistance	R _g	f = 1 MHz		0.4	1.0	2.0	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -20 V, R _L = 3 Ω, I _D ≅ -10 A, V _{GEN} = -10 V, R _g = 1 Ω		-	18	27	ns
Rise time ^c	t _r			-	7	11	
Turn-off delay time ^c	t _{d(off)}			-	56	84	
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	-350	A
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V		-	-0.76	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -10 A, di/dt = 100 A/μs		-	26	52	ns
Body diode reverse recovery charge	Q _{rr}			-	22	44	nC
Reverse recovery fall time	t _a			-	15	-	ns
Reverse recovery rise time	t _b			-	11	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.6	-	A

Notes

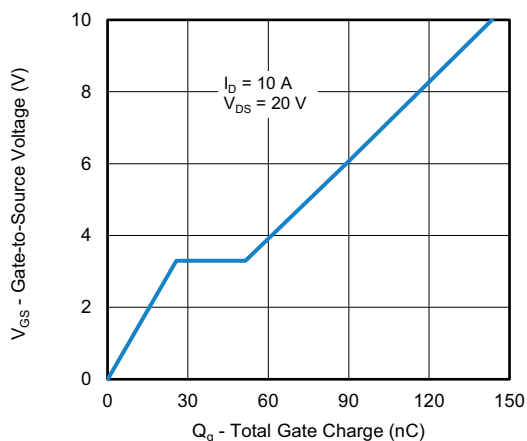
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

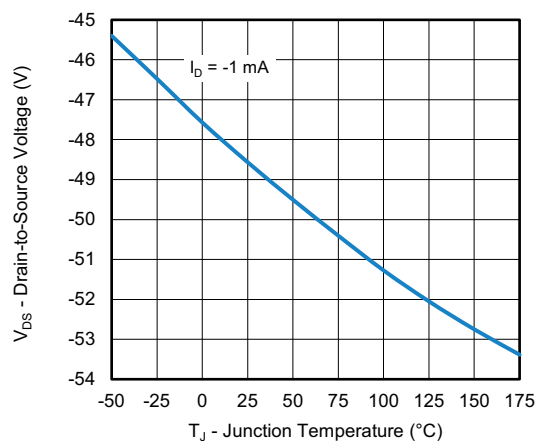
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Capacitance

Transconductance

On-Resistance vs. Drain Current



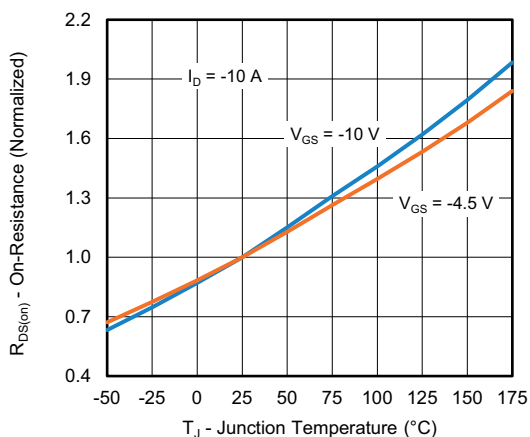
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



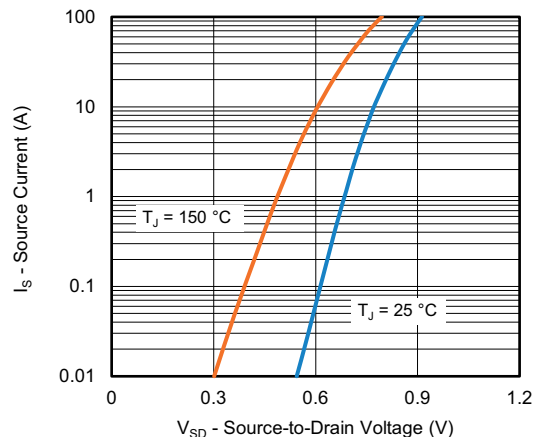
Gate Charge



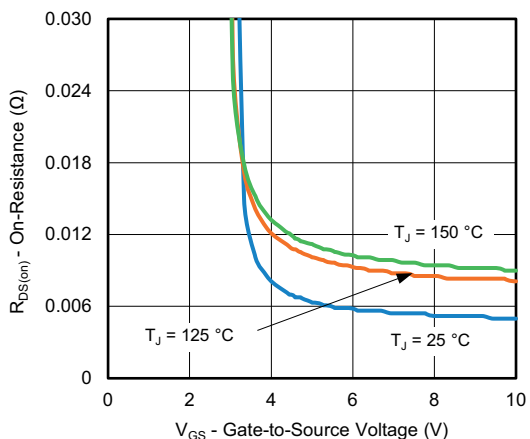
Drain-Source Breakdown vs. Junction Temperature



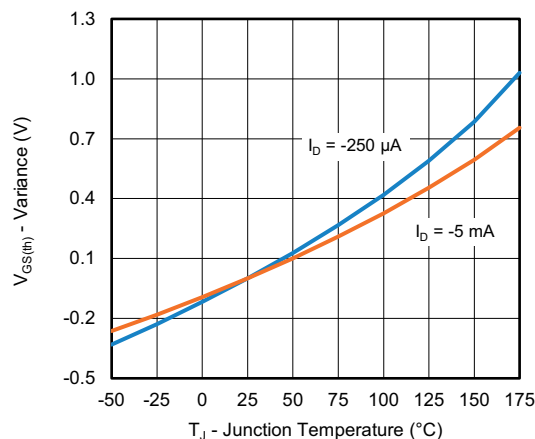
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



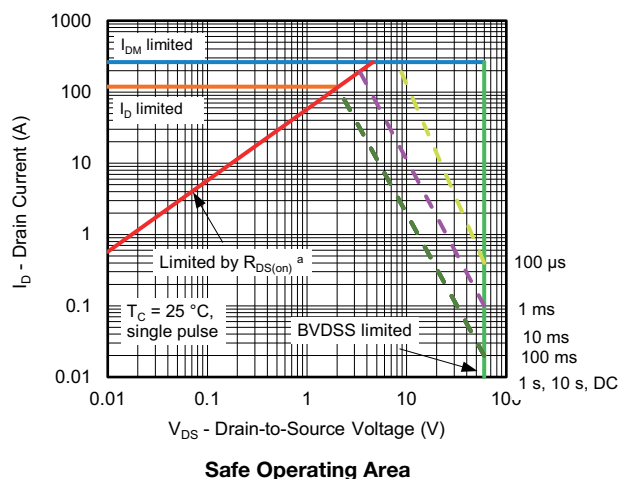
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



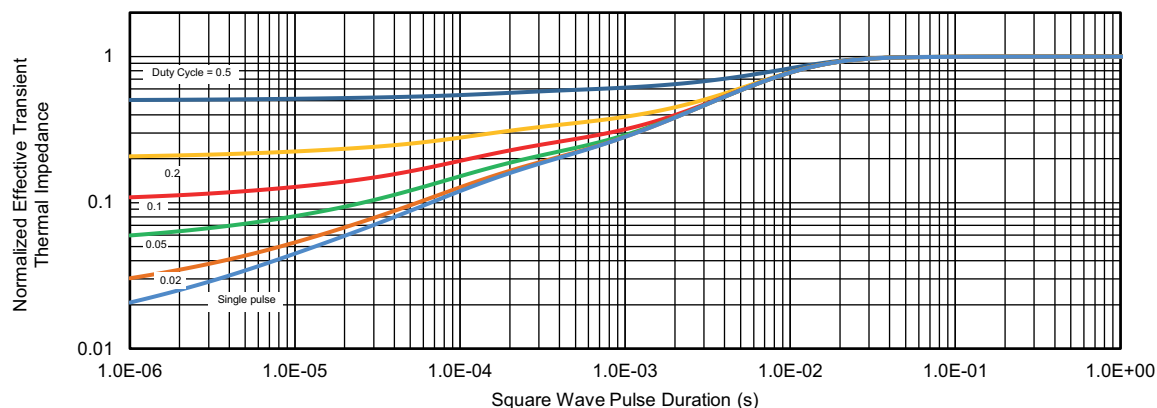
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



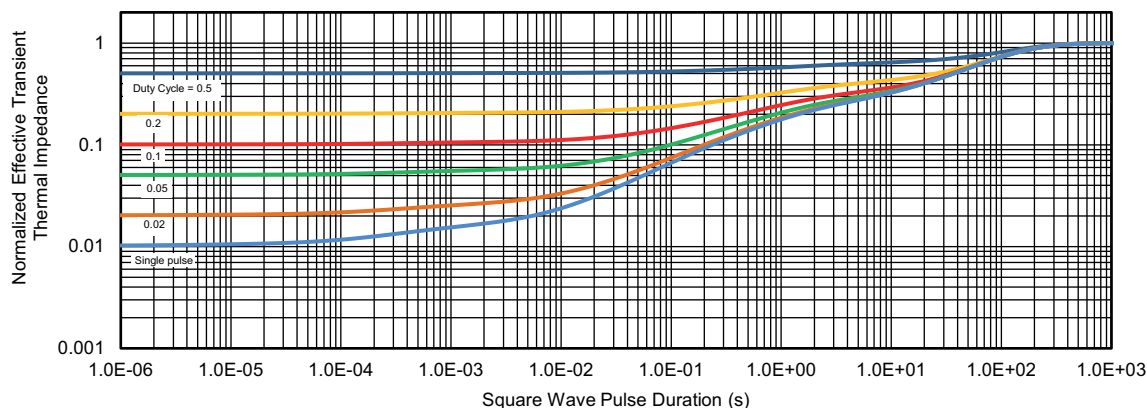
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

THERMAL RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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